Test Beam Characterisation of stitched CMOS Strip Sensors

Naomi Davis on behalf of the CMOS Strips Collaboration

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Fachhochschule Dortmund University of Applied Sciences and Arts







Single-Vendor Problem

- Silicon sensors have become indispensable in high energy physics.
- ... only available from few foundries

Alternative vendors ?

- Vendor diversification through standardised industrial CMOS process
- Fast, cheap and large-scale production

CMOS Strip Sensors

- n-in-p sensor, 150 nm LFoundry technology
- 150 ± 10 um thickness, 75.5 um strip pitch
- Different formats through stitching technique









CMOS Strip Sensors

• Strip-implant varies in width and doping concentration



DESY II TB Facility

ADENIUM telescope + CMS plane

e^- beam energy: 4.6 GeV



111

Pink Box with DUT

0

6

Adenium Telescope

Scintillators

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111

Pink Box with DUT

0

6

Adenium Telescope

Scintillators

DUT Cooling – ITk Box

- Cooling with dry ice pellets to $-45^{\circ}C$
- Limited run time of 1.5h
- Temperature and position fluctuations





Sensor position fluctuation

DUT Cooling – 'Pink' Box

- Reduced box dimensions
- Cooling with stacked Peltier elements connected to chiller





Universität freiburg

DUT Cooling – 'Pink' Box

- Sensor held by copper PCB (cooling)
- Reduced material budget





DUT Cooling – 'Pink' Box



Temperature in ITk Box (on sensor board)



Temperatur in Pink Box (air)



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In-Strip Hit Detection Efficiency

Efficiency within the strip @threshold[SNR] = 5

• Homogeneous efficiency along strip length





In-Strip Mean Absolute Deviation (MAD)

MAD within the strip @threshold[SNR] = 5

Hit position residual MAD = $\sum |x_{track} - x_{cluster}|$ ullet

Regular

Stitching

Deprecated resolution towards strip edges (no full depletion) ullet

LD 30



LD 55

n

Sample **1e16** n_{eq}/cm² @500V bias

Neutron Irradiated Short

In-Strip Hit Detection Efficiency

Efficiency within the strip @threshold[SNR] = 5

- Strong efficiency decrease (no full depletion)
- No stitching effect at high fluences

Stitching



Neutron Irradiated Short Sample

 $1e16 n_{eq}/cm^2@500V bias$



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LD 55

0

14

Conclusion & Outlook

What we have learned and what's next ...

- Stitching does not impact resolution and hit detection efficiency!
 - Efficiency drop for LD designs and irradiated samples
- Improved setup for more efficient data taking
- Further Investigations:
 - Comparison to proton irradiation, charge calibration
- Active sensor submission under discussion

Thank you, Questions?

Naomi Davis, Jan-Hendrik Arling, Marta Baselga, Leena Diehl, Jochen Dingfelder, Ingrid M. Gregor, Marc Hauser, Fabian Hügging, Tomasz Hemperek, Karl Jakobs, Michael Karagounis, Roland Koppenhöfer, Kevin Kröninger, Fabian Lex, Ulrich Parzefall, Arturo Rodriguez, Birkan Sari, Niels Sorgenfrei, Simon Spannagel, Dennis Sperlich, Tianyang Wang, Jens Weingarten, Iveta Zatocilova

> The measurements leading to these results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF).